## 1. General description

PNP high-voltage low  $V_{CEsat}$  transistor in a SOT89 (SC-62) small and flat Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	-	-200	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-150	V
I <sub>C</sub>	collector current		-	-	-1	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C	100	220	-	

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		В—
3	В	base	3 2 1 SOT89	E sym079



# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package							
	Name	Description	Version					
PBHV9115X-Q		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89					

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBHV9115X-Q	%4G

<sup>[1] % =</sup> placeholder for manufacturing site code

## 8. Limiting values

#### Table 5. Limiting values

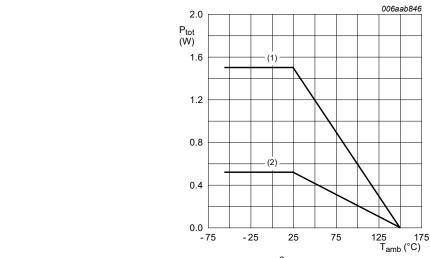
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-200	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-150	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-200	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	А
I <sub>BM</sub>	peak base current			-	-400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	520	mW
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBHV9115X-Q

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

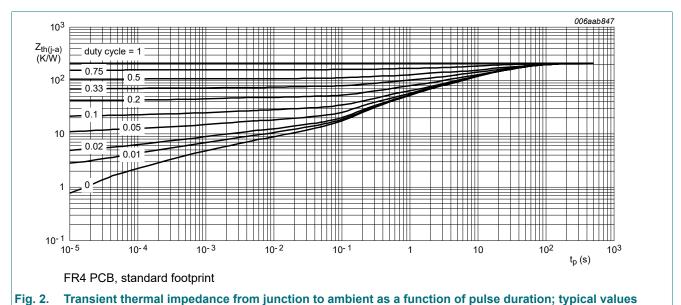
Fig. 1. Power derating curves

## 9. Thermal characteristics

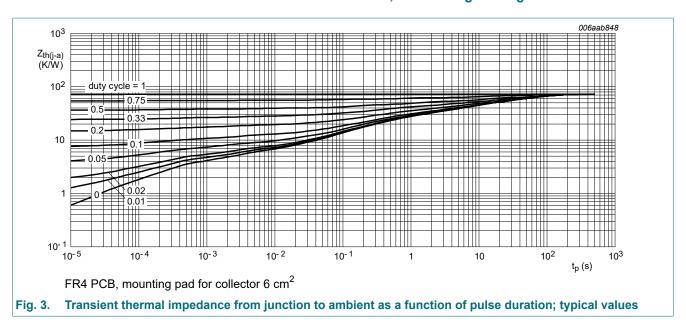
**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	240	K/W
junction to an	junction to ambient		[2]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



### 150 V, 1 A PNP high-voltage low VCEsat transistor



## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	$V_{CB} = -120 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -120 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C	100	220	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	220	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	30	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -10 mA; $T_{amb}$ = 25 °C	-	-60	-120	mV
		$I_C$ = -100 mA; $I_B$ = -20 mA; $T_{amb}$ = 25 °C	-	-50	-100	mV
		$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C	-	-200	-300	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-1	-1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -6 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -0.1 A;	-	8	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C	-	282	-	ns
t <sub>on</sub>	turn-on time		-	290	-	ns
t <sub>s</sub>	storage time		-	430	-	ns
t <sub>f</sub>	fall time		-	300	-	ns
t <sub>off</sub>	turn-off time		-	730	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	115	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	10	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB}$ = -0.5 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	150	-	pF

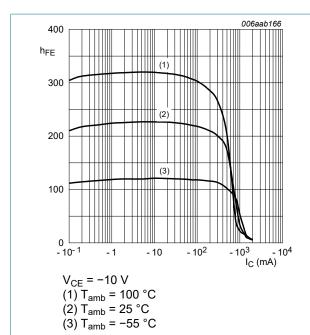


Fig. 4. DC current gain as a function of collector current; typical values

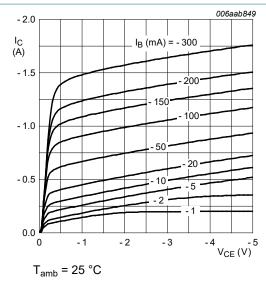


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

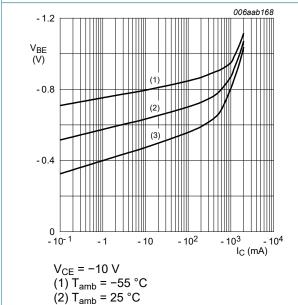
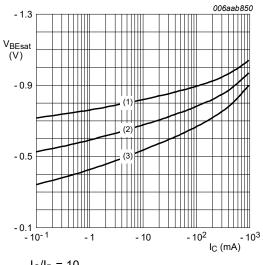


Fig. 6. Base-emitter voltage as a function of collector current; typical values

(3)  $T_{amb} = 100 \, ^{\circ}C$ 



 $I_{\rm C}/I_{\rm B} = 10$ (1)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = 100~{\rm ^{\circ}C}$ 

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

V<sub>CEsat</sub>

### 150 V, 1 A PNP high-voltage low VCEsat transistor

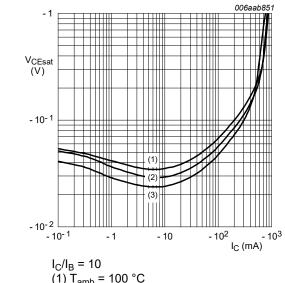
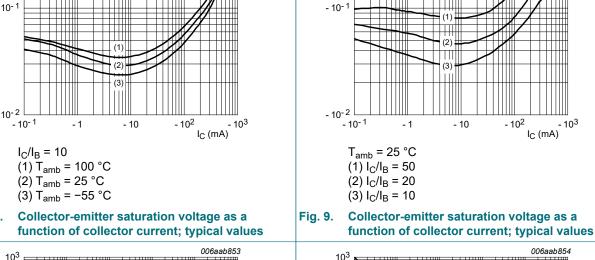
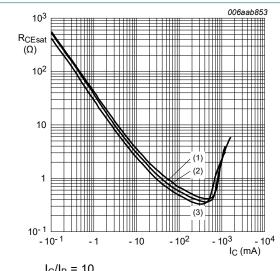


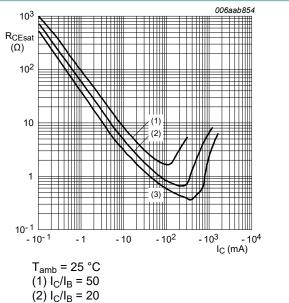
Fig. 8.





 $I_{\rm C}/I_{\rm B} = 10$ (1)  $T_{amb}$  = 100 °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



(3)  $I_C/I_B = 10$ 

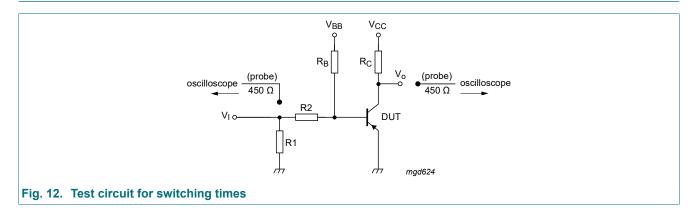
Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

6/11

- 10<sup>3</sup>

## 150 V, 1 A PNP high-voltage low VCEsat transistor

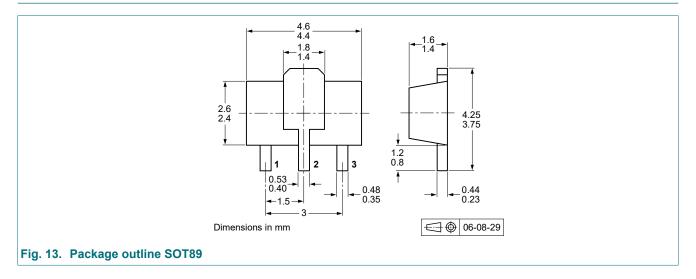
## 11. Test information



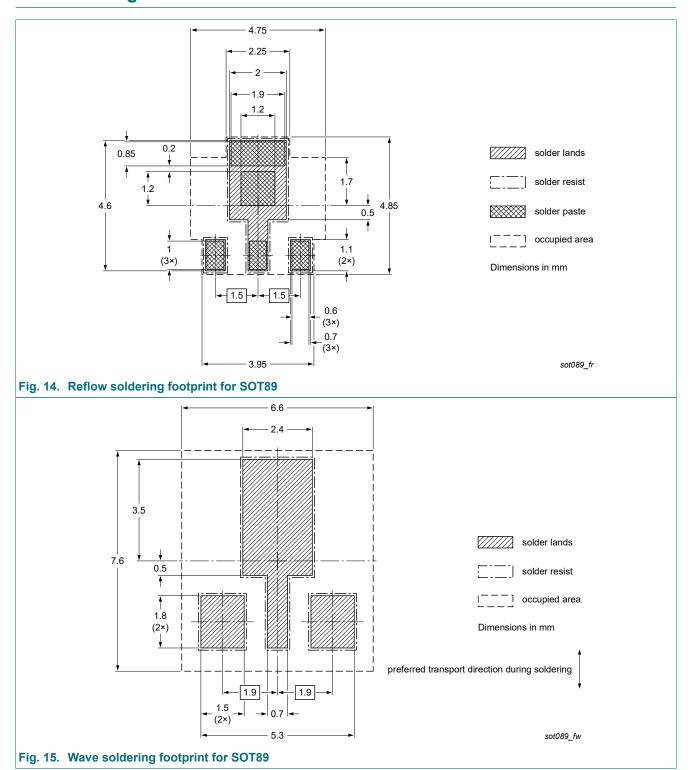
## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



# 13. Soldering



## 150 V, 1 A PNP high-voltage low VCEsat transistor

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115X-Q v.1	20230717	Product data sheet	-	-

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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	Features and benefits

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